

In the Claims:

Please amend claims 12, 17, and 19. The claims are as follows:

1-11. (Withdrawn)

12. (Currently Amended) A transistor comprising:

a) a transistor body formed on a substrate, the transistor body having a first vertical edge

and a second vertical edge;

b) a gate structure adjacent in direct mechanical contact with the transistor body first vertical edge;

c) a body contact structure adjacent the transistor body second vertical edge and aligned with the gate;

d) a bridge over the body, the gate, and the body contact, electrically connecting the gate and the body contact; and

c) source and drain regions in the body on opposite ends of the body.

13. (Original) The transistor of claim 12 wherein the gate structure comprises p-type material and wherein the body contact structure comprises n-type material.

14. (Original) The transistor of claim 12 wherein the gate structure comprises n-type material and wherein the body contact structure comprises p-type material.

15. (Original) The transistor of claim 12 wherein the transistor body comprises a portion of silicon of the silicon-on-insulator layer.

16. (Original) The transistor of claim 12 wherein the thickness of the transistor body between the gate structure and the body contact structure is less than one-third of the length of the gate structure.

17. (Currently Amended) The transistor of claim 12 further comprising A transistor comprising:

a) a transistor body formed on a substrate, the transistor body having a first vertical edge and a second vertical edge;

b) a gate structure adjacent the transistor body first vertical edge;

c) a body contact structure adjacent the transistor body second vertical edge and aligned with the gate;

d) a bridge over the body, the gate, and the body contact, electrically connecting the gate and the body contact;

e) source and drain regions in the body on opposite ends of the body;

f) a gate dielectric between the transistor body first edge and the gate structure; and

g) a diffusion barrier between the transistor body second edge and the body contact structure.

18. (Original) The transistor of claim 12 wherein the transistor body comprises source and drain implants into the transistor body, the implants aligned with the edges of the body contact and the

gate structure.

19. (Currently Amended) The transistor of claim 12 A transistor comprising:

a) a transistor body formed on a substrate, the transistor body having a first vertical edge and a second vertical edge;

b) a gate structure adjacent the transistor body first vertical edge;

c) a body contact structure adjacent the transistor body second vertical edge and aligned with the gate;

d) a bridge over the body, the gate, and the body contact, electrically connecting the gate and the body contact; and

e) source and drain regions in the body on opposite ends of the body, wherein the body comprises widened end portions that are insulated from the gate and the body contact.

20. (Original) The transistor of claim 12 wherein the transistor body first edge is opposite the transistor body second edge and wherein the transistor body first edge and transistor body second edge are substantially perpendicular to a top surface of the substrate.

21. (Original) A dynamic threshold complimentary metal oxide semiconductor field effect transistor comprising:

- a) a transistor body, the transistor body formed from a silicon layer formed above an insulator layer, the transistor body having a first vertical edge and a second vertical edge, wherein the transistor body first edge and the transistor body second edge are opposite each other and substantially perpendicular to the insulator layer, thereby defining a fin-type transistor body;
- b) a gate dielectric layer formed on the transistor body first edge;
- c) a body contact native oxide layer formed on the transistor body second edge;
- d) a gate structure formed on the gate dielectric layer adjacent to the transistor body first edge, the gate structure comprising p-type polysilicon; and
- e) a body contact structure formed on the body contact native oxide layer aligned to the gate structure and adjacent to the transistor body second edge, the body contact structure comprising n-type polysilicon.

22. (Original) A dynamic threshold complimentary metal oxide semiconductor field effect transistor of claim 21 wherein the gate structure comprises n-type polysilicon and the body contact structure comprises p-type polysilicon.

23. (Original) The dynamic threshold complimentary metal oxide semiconductor field effect transistor of claim 21 wherein the body comprises a substantially uniform dopant concentration density in the source and drain regions.

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24. (Original) The dynamic threshold complimentary metal oxide semiconductor field effect transistor of claim 23 wherein the substantially uniform dopant concentration density is formed by performing a plurality of angled implants into the transistor body.

25. (Original) The dynamic threshold complimentary metal oxide semiconductor field effect transistor of claim 21 further comprising a metal silicide bridge over the body to electrically couple the gate structure to the body contact structure.